

AMENDMENTS TO THE CLAIMS

Please amend claims 1 and 13 as set forth below.

1. (CURRENTLY AMENDED) A semiconductor device comprising:
a semiconductor substrate;
a high-dielectric-constant film on the semiconductor substrate; and
a nitride layer on the high-dielectric-constant film,
wherein the high-dielectric constant film is selected from film comprised of enhanced dielectric materials including Al_2O_3 , ZrO_2 , HfO_2 , Al_2O_3 and PrO_2 , silicate film derived from said enhanced dielectric materials, film having multi-element materials including a combination of at least two of Al_2O_3 , ZrO_2 , HfO_2 , Al_2O_3 and PrO_2 , and film having multi-layered structures including at least two layers of said silicate film.
2. (PREVIOUSLY PRESENTED) The semiconductor device according to claim 1, further comprising:
a p-type impurity-contained layer on the nitride layer.
3. (PREVIOUSLY PRESENTED) The semiconductor device according to claim 1, wherein the nitride layer is formed by introducing nitrogen into a top surface portion of the high-dielectric-constant film.
4. (PREVIOUSLY PRESENTED) The semiconductor device according to claim 1, wherein the semiconductor substrate is a silicon substrate or a silicon layer.
5. (PREVIOUSLY PRESENTED) The semiconductor device according to claim 2, wherein the p-type impurity-contained layer is a boron-contained silicon layer.

Claims 6 – 12 are (CANCELED).

13. (CURRENTLY AMENDED) A semiconductor device comprising:
a semiconductor substrate;
a gate insulating film on the semiconductor substrate; and
a gate electrode formed on the gate insulating film and including at least a p-type impurity-contained layer,

wherein the gate insulating film includes a high-dielectric-constant film and a nitride layer on the high-dielectric-constant film, and

wherein the high-dielectric constant film is selected from film comprised of enhanced dielectric materials including Al_2O_3 , ZrO_2 , HfO_2 , Al_2O_3 and PrO_2 , silicate film derived from said enhanced dielectric materials, film having multi-element materials including a combination of at least two of Al_2O_3 , ZrO_2 , HfO_2 , Al_2O_3 and PrO_2 , and film having multi-layered structures including at least two layers of said silicate film.

14. (PREVIOUSLY PRESENTED) The semiconductor device according to claim 13, wherein the nitride layer is formed by introducing nitrogen into a top surface portion of the high-dielectric-constant film.

15. (PREVIOUSLY PRESENTED) The semiconductor device according to claim 13, wherein the semiconductor substrate is a silicon substrate or a silicon layer.

16. (PREVIOUSLY PRESENTED) The semiconductor device according to claim 13, wherein the p-type impurity-contained layer is a boron-contained silicon layer.

Claims 17 – 22 are (CANCELED).